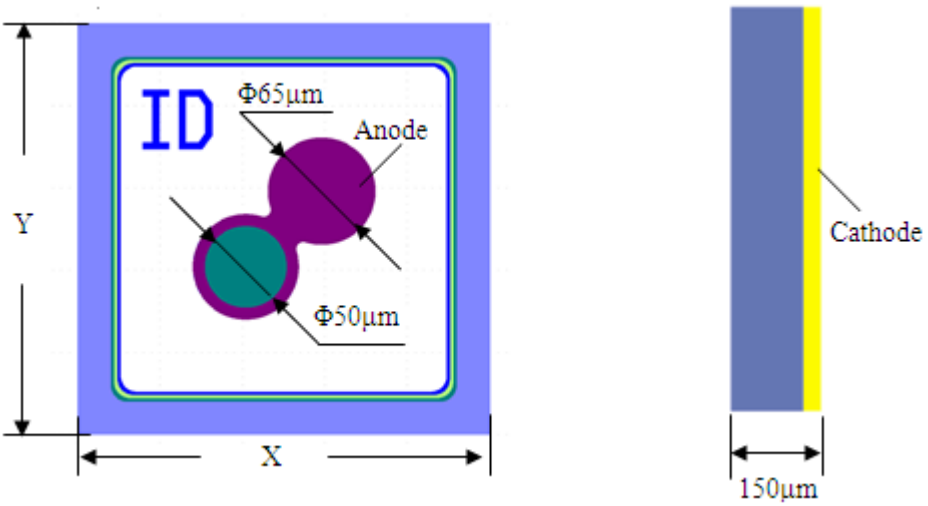
S-10AAPD01-G InGaAs/InP APD 芯片特性参数

♦ Physical Parameters:



Die Dimension		Pad Diameter	Aperture Diameter	Die Thickness
X	Y			
250 μm	250 μm	65 μm	50 μm	150 μm

♦ Specifications（T=25^{0}C）:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Wavelength Range	λ		910	1310/1550	1650	nm
Breakdown Voltage	V_{BR}	I_D=10μA	38			V
Punch-through Voltage	V_P	λ=1550nm P_O=1μW M=1.1	20		30	V
Range of Operation Voltage	ΔV_{OP}	$\Delta V_{OP} = V_{BR} - V_P$	18			V
Dark Current	I_D	$V_R = V_{BR}$-3V			20	nA
Multiplication Factor	M	λ=1550nm P_O=1μW $V_R = V_{BR}$-3V	10			
Capacitance	C	$V_R = V_{BR}$-3V			0.5	pF
-3dB Bandwidth	BW	$V_R = V_{BR}$-3V λ=1550nm	2.5			GHz